

IMPURITIES AND THEIR RADIATION EFFECTS ON THE PERFORMANCE OF QUARTZ OSCILLATOR CRYSTALS FOR ONBOARD SATELLITE COMMUNICATION

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Because of their high Q ($\sim 2-3$ million) and because of their high Q integral part of all the frequency control appliances. The type and concentration of the impurities present in the quartz is trivalent aluminum which occupies the substitutional sites of tetra-valent aluminum center therefore becomes an electron excess aluminum center therefore becomes a compensation. These charge compensators are usually monovalent ionic impurities located at interstitial sites. Since quartz is grown from a melt, it becomes an ubiquitous impurity in the form of interstitial protons around aluminum as charge compensators. The other charge compensators at aluminum sites include impurities such as sodium, which are derived from the mineralizer solution and get incorporated in the crystal. These defects give rise to the internal losses in the crystalline material. When exposed to radiation, quartz oscillators exhibit both transient and steady state frequency shifts and Q losses. Depending upon the type and concentration of impurities, the losses type and concentration vary. After the irradiation is over, it is only after some time that the crystal resumes its oscillations.

This paper describes the results of our studies on the radiation effects on the material selection and its post-growth treatment for achieving the desired performance of quartz oscillator crystals. Such crystals would find application in satellite-borne frequency standards. Results of our studies on characterization of various grades of natural and cultured quartz crystals for their irradiation induced changes will be presented. The results show that during the 300 K-irradiation both protons as well as the alkali move away from their original positions under the influence of radiation. Thus, irradiation at 300 K leads to the formation of a mixture of Al-hole and Al-OH centers. These centers can be monitored for monitoring the radiation-induced changes. Our characterization methods include measurement of transient and steady-state frequency and Q losses, infrared absorption (sweeping). The irradiation sequence has been carried out on various grades of natural and cultured quartz crystals. The current understanding is that Al, Al-hole, and high mechanical Q crystals should be the preferred material for use in satellite-borne frequency standards.

